

Prospective Data

Insulated Gate Bi-Polar Transistor Type T0800TB45E

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	4500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	2800	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	800	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	1600	A
I_{ECO}	Maximum reverse emitter current, $t_p=100\mu s$, (note 2 & 3)	800	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	6.4	KW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	1500	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) The use of an anti-parallel diode is recommended.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	2.8	3.2	$I_C = 800A, V_{GE} = 15V, T_J = 25^\circ C$	V
		-	3.5	3.9	$I_C = 800A, V_{GE} = 15V$	V
V_{T0}	Threshold voltage	-	-	1.71	Current range: 265 – 800A	V
r_T	Slope resistance	-	-	2.74		m Ω
$V_{GE(TH)}$	Gate threshold voltage	-	5.3	-	$V_{CE} = V_{GE}, I_C = 85mA$	V
I_{CES}	Collector – emitter cut-off current	-	10	35	$V_{CE} = V_{CES}, V_{GE} = 0V$	mA
I_{GES}	Gate leakage current	-	-	± 10	$V_{GE} = \pm 20V$	μA
C_{ies}	Input capacitance	-	135	-	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	nF
$t_{d(on)}$	Turn-on delay time	-	2	-	$I_C = 800A, V_{CE} = 2800V, di/dt = 1500A/\mu s$ $V_{GE} = \pm 15V, L_g = 200nH$ $R_{g(ON)} = 8.2\Omega, R_{g(OFF)} = 8.2\Omega, C_{GE} = 68nF$ Freewheel diode type E0900NC45C at $T_J = 125^\circ C$. (Notes 3, 4 & 5)	μs
$t_r(V)$	Rise time	-	4	-		μs
$Q_{g(on)}$	Turn-on gate charge	-	5	-		μC
E_{on}	Turn-on energy	-	7	-		J
$t_{d(off)}$	Turn-off delay time	-	4.5	-		μs
$t_f(I)$	Fall time	-	2.1	-		μs
$Q_{g(off)}$	Turn-off gate charge	-	9	-		μC
E_{off}	Turn-off energy	-	4.3	-		J
I_{SC}	Short circuit current	-	2500	-	$V_{GE} = \pm 15V, V_{CE} = 2800V, V_{CEmax} \leq V_{CES}, t_p \leq 10\mu s$	A

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	15.6	Double side cooled	K/kW
		-	-	25.6	Collector side cooled	K/kW
		-	-	40.6	Emitter side cooled	K/kW
F	Mounting force	15	-	25	Note 2	kN
W_t	Weight	-	1.2	-		kg

Notes:-

- 1) Unless otherwise indicated $T_J = 125^\circ C$.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) E_{on} integration time 15 μs from 10% rising I_C .
- 5) E_{off} integration time 15 μs from 90% falling V_{GE} .

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

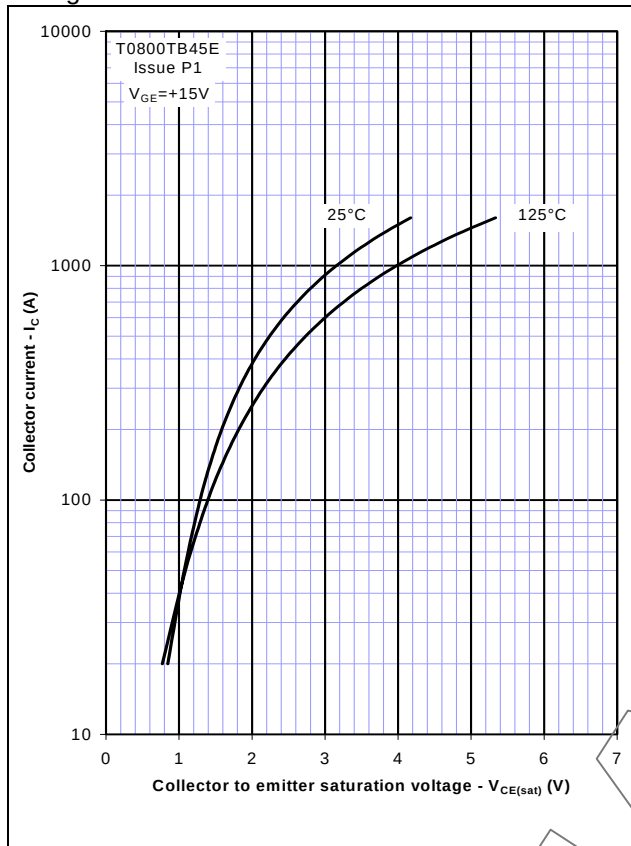


Figure 2 – Typical output characteristic

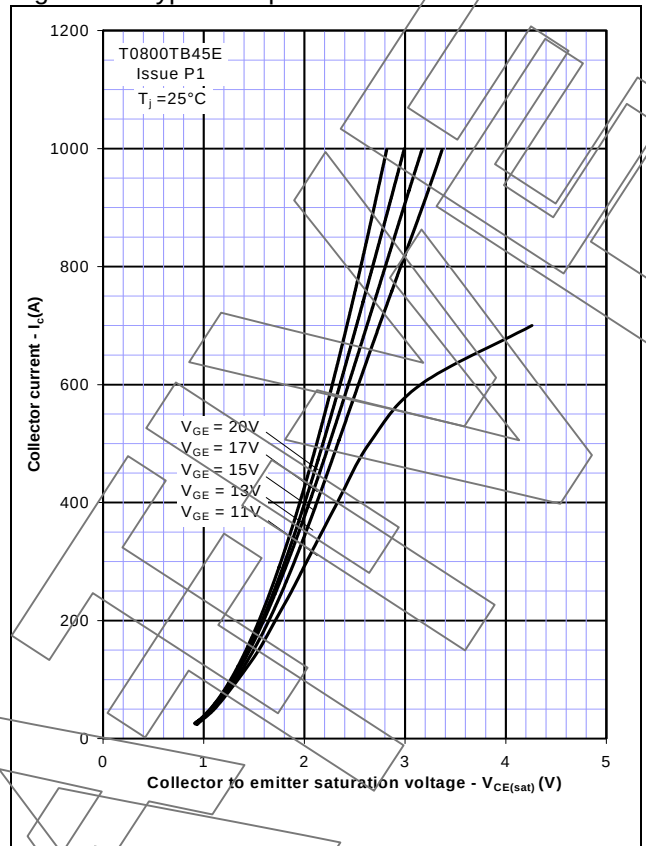


Figure 3 – Typical output characteristic

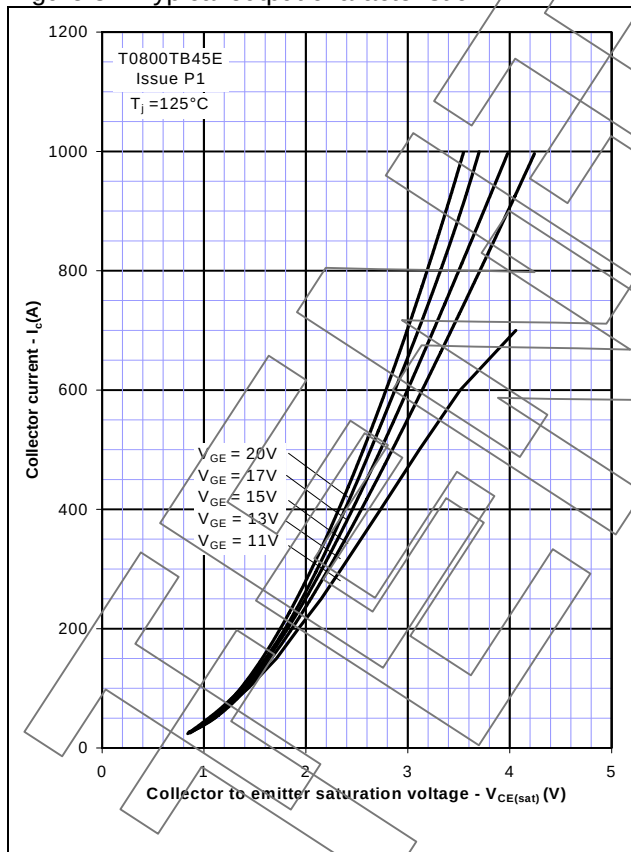


Figure 4 – Typical turn-on delay time vs gate resistance

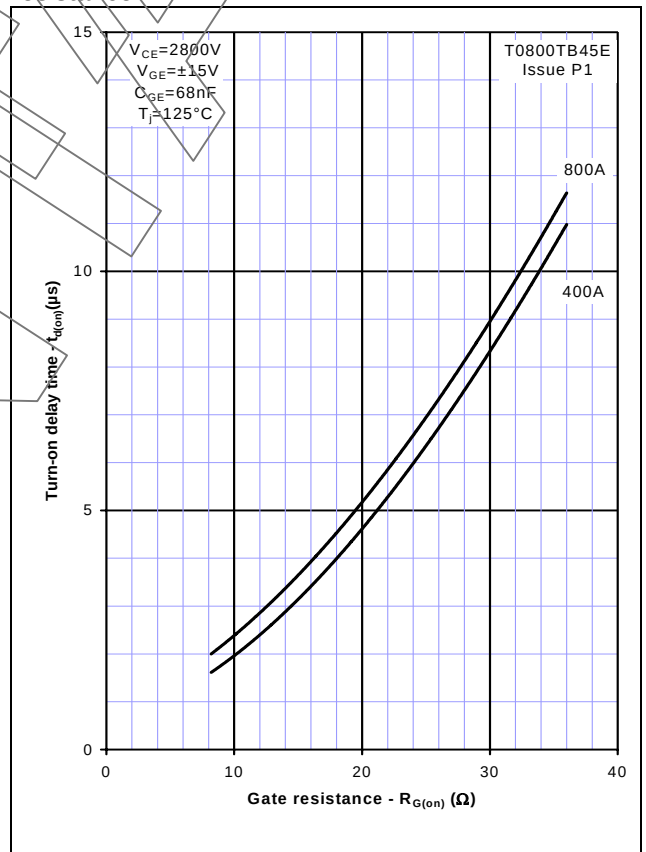


Figure 5 – Typical turn-off delay time vs. gate resistance

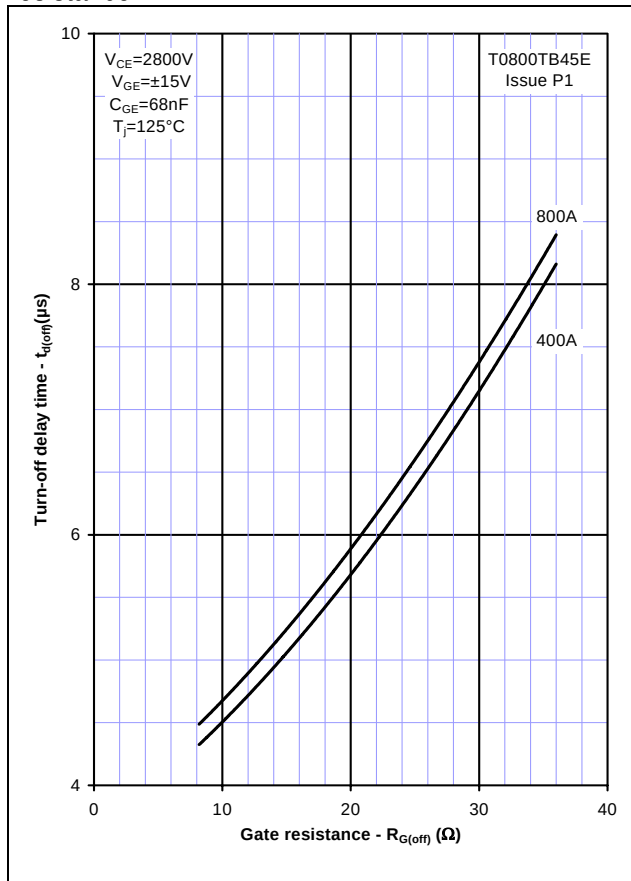


Figure 6 – Typical turn-on energy vs. collector current

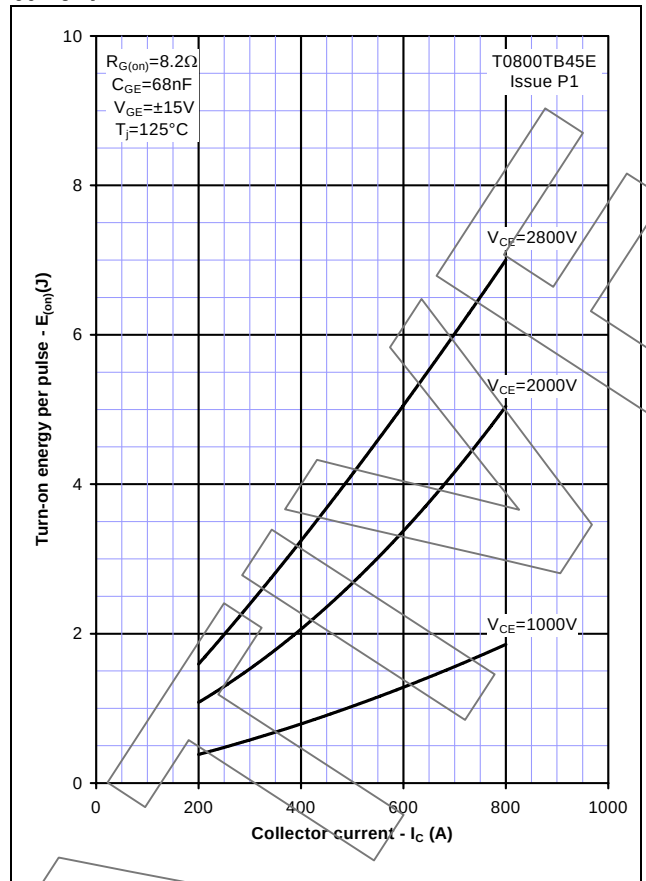


Figure 7 – Typical turn-on energy vs. di/dt

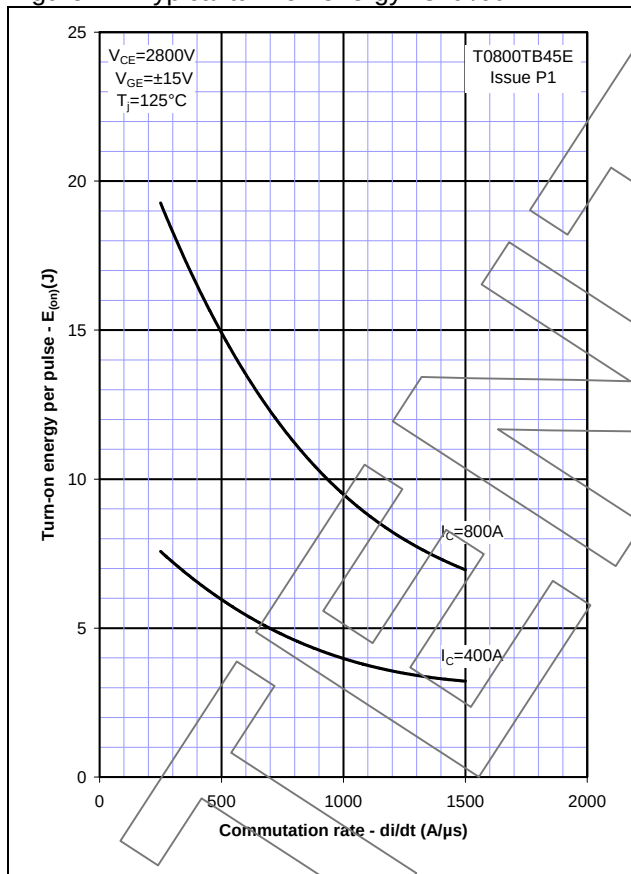


Figure 8 – Typical turn-off energy vs. collector current

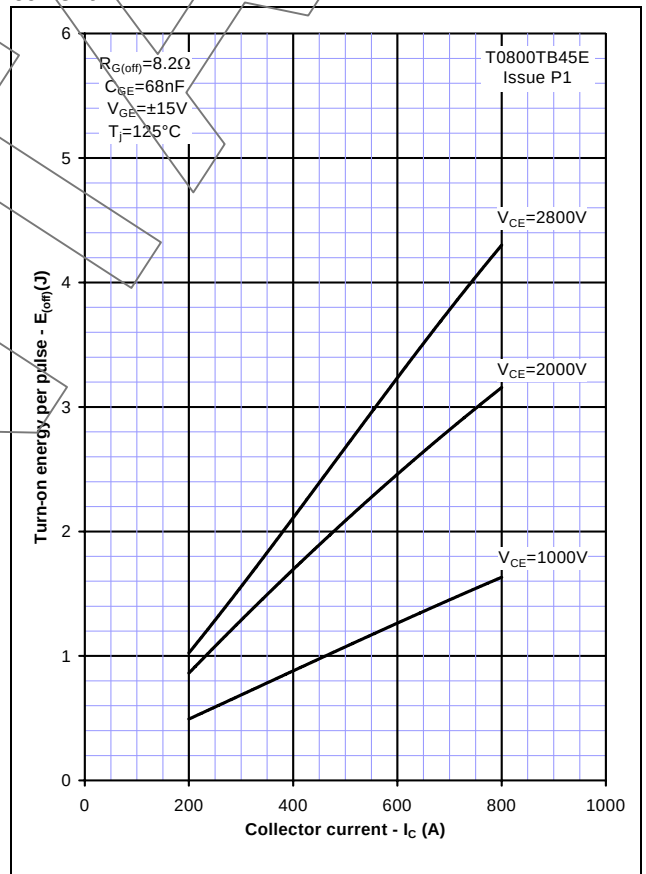


Figure 9 – Turn-off energy vs voltage

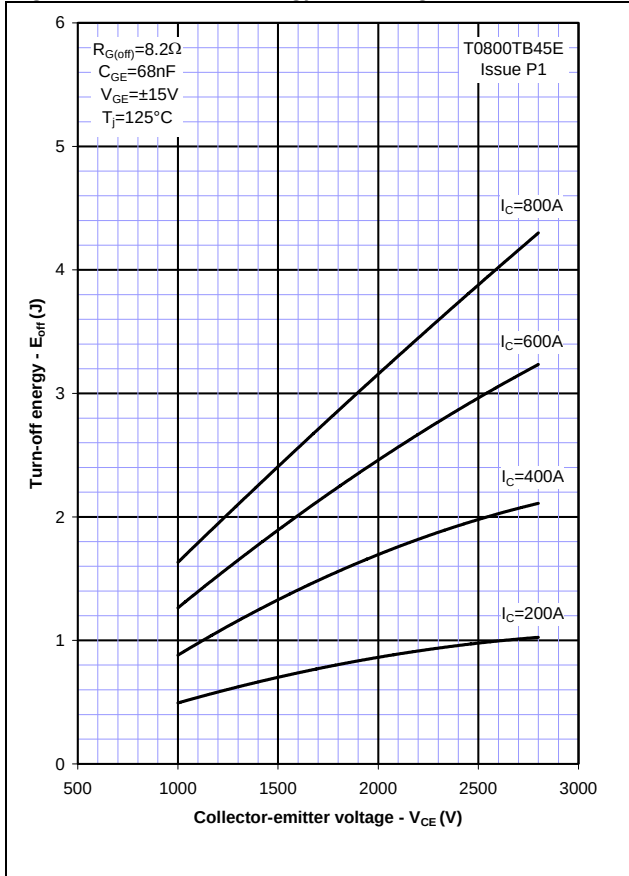


Figure 10 – Safe operating area

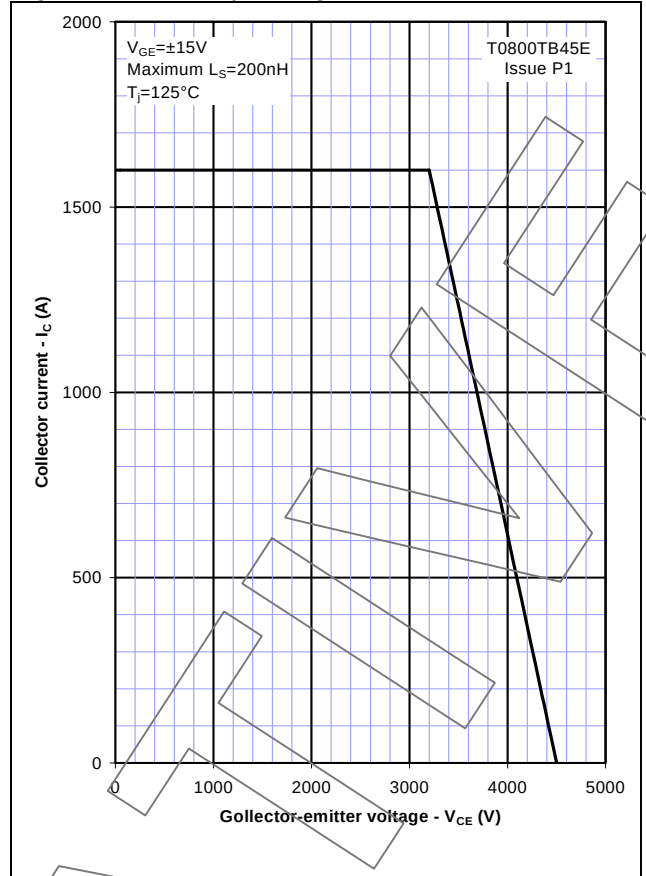
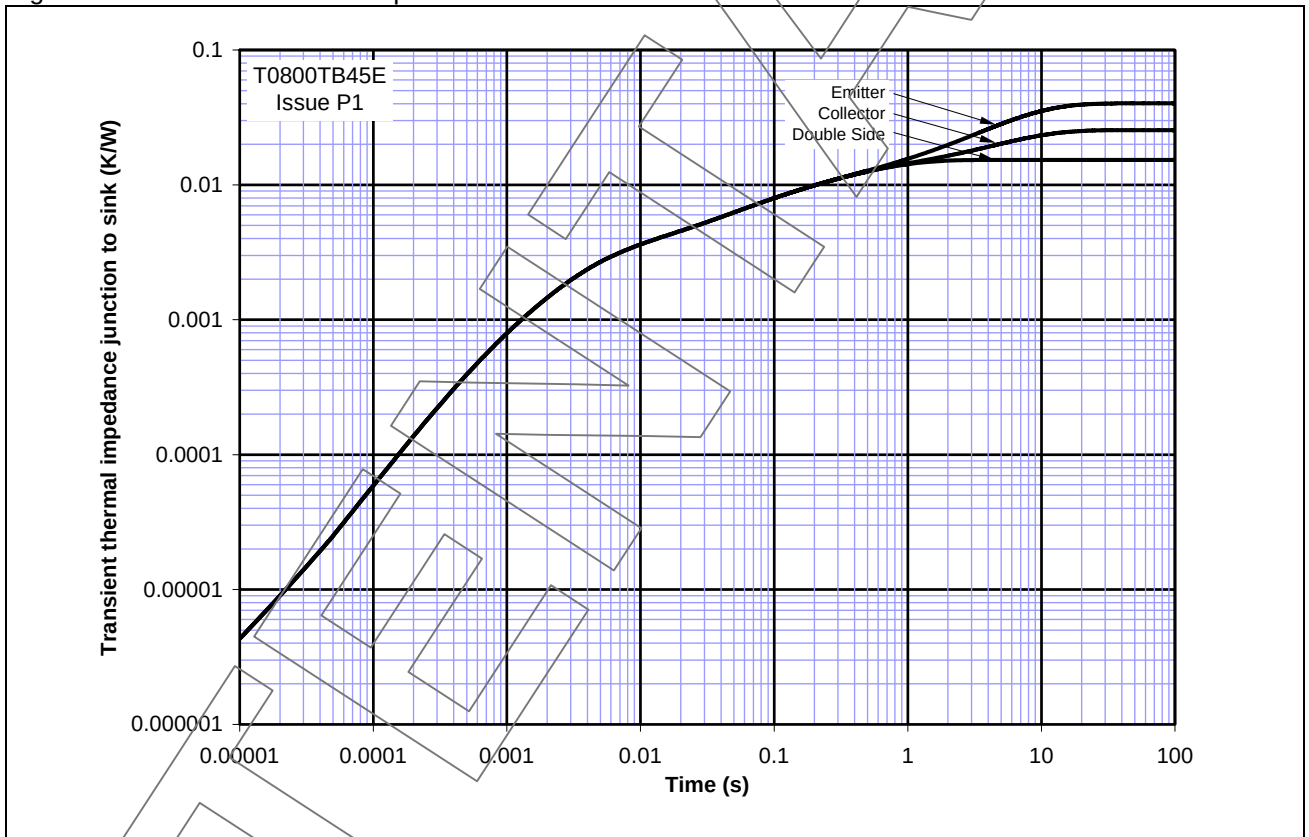


Figure 11 – Transient thermal impedance



Technical drawing of the 171A108 vacuum tube, showing top and side views with dimensions and labels.

Top View Dimensions and Labels:

- $\phi 3.6/3.5 \times 2$ MIN DEPTH 2-HOLES, ONE IN EMITTER AND ONE IN COLLECTOR.
- GATE / EMITTER & MONITORING TERMINATIONS: STANDARD TABS 4.75×0.5 THICK
- GATE LIES BENEATH MONITORING TAB
- EMITTER
- 65 MAX (BOTH TABS)

Side View Dimensions and Labels:

- $\phi 112$ (Overall diameter)
- $\phi 75$ (Collector diameter)
- 0.8 MIN (Collector thickness)
- COLLECTOR
- MONITORING TAB
- 0.8 MIN (Monitoring tab thickness)
- 4 TYP (Number of monitoring tabs)
- EMITTER
- 26 ± 0.5 COMPRESSED HEIGHT
- $\phi 75$ (Emitter diameter)
- MIN CREEP PATH OVER CONVOLUTIONS = 35.

Part Number: 171A108

(Please quote 10 digit code as below)

T0800	TB	45	E
Fixed type Code	Fixed Outline Code	Voltage Grade V _{CES} /100 45	Fixed format code

Typical order code: T0800TB45E ($V_{CES} = 4500V$)

WESTCODE

An IXYS Company

IXYS Corporation
1590 Buckeye Drive
Milpitas CA 95035-7418
Tel: +1 (408) 457 9000
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

~~www.westcode.com~~

www.ixys.net

IXYS Long Beach
IXYS Long Beach, Inc.
2500 Mira Mar Ave, Long Beach
CA 90815
Tel: +1 (562) 296 6584
Fax: +1 (562) 296 6585
E-mail: service@ixyslongbeach.com

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